Effect of NH₄F additive on the electrical properties of nanosized tin dioxide films obtained from lyophilic and lyophobic film-forming systems

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Composite systems based on tin dioxide have many applications as a functional material [1, 2]. In this case, the properties of the resulting film can significantly depend on the method of obtaining a thin film. In this work, we studied the effect of NH₄F addition on the electrical properties of nanosized tin dioxide films obtained from lyophilic and lyophobic film-forming systems. Thin films of tin dioxide were obtained from 5 film-forming systems, including those containing NH₄F and NH₄OH dopants: SnCl₄/EtOH, SnCl₄/EtOH/NH₄F, SnCl₄/EtOH/NH₄OH, SnO₂/EtOH, SnO₂/EtOH/NH₄F. For a assessment of the contribution of doping additives to the conductivity of the films, calculations of the surface resistance, resistivity, and conductivity of the films under study were made. The results are presented in Table 1.

Table 1 – Surface resistance, resistivity, specific conductivity of the studied films

The composition of the film-forming system	R _{sh} , kOm/ square	ρ, Om*cm	1/ρ, Om ⁻¹ *cm ⁻¹
SnCl ₄ /EtOH	15,6±1,4	0,390±0,035	2,6±0,2
SnCl ₄ /EtOH/NH ₄ F	$6,7\pm0,6$	$0,097\pm0,008$	10,3±0,8
SnCl ₄ /EtOH/NH ₄ OH	15,4±1,6	0,255±0,026	3,9±0,4
SnO ₂ /EtOH	78,9±6,9	0,512±0,044	1,9±0,2
SnO ₂ /EtOH/NH ₄ F	69,4±8,3	0,590±0,070	1,7±0,2

Table 1 shows that the addition of NH₄F to the lyophobic film-forming system SnO₂/EtOH did not lead to an increase in the specific conductivity. At the same time, the addition of NH₄F to the lyophilic film-forming system SnCl₄/EtOH leads to an increase in the specific conductivity by several times. This confirms the presence of fluorine ions as additional sources of free charge carriers in the composition of the films [3]. The addition of an aqueous ammonia solution to the SnCl₄/EtOH/NH₄OH film-forming system also led to an increase in the specific conductivity. Apparently, due to an unshared electron pair in the nitrogen atom.

X-ray diffraction analysis confirmed the presence of fluorine ions in the films obtained from the $SnCl_4/EtOH/NH_4F$ film-forming systems. The X-ray diffraction pattern are shown in Figure 1. It can be seen that all films consist of SnO_2 crystallites. On the X-ray diffraction pattern of the film obtained from the $SnCl_4/EtOH/NH_4F$ film-forming system, $SnOF_2$ peaks are observed. These peaks indicates the successful incorporation of tin ions into the film structure.

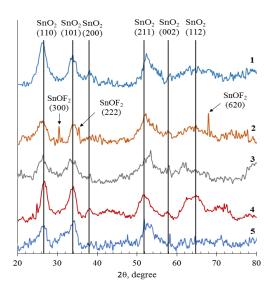


Figure 1 – X-ray patterns of thin films of tin dioxide obtained from different film-forming systems: 1 - SnCl₄/EtOH, 2 - SnCl₄/EtOH/NH₄F, 3 - SnCl₄/EtOH/NH₄OH, 4 - SnO₂/EtOH, 5 - SnO₂/EtOH/NH₄F

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